

**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

3. (amended) A silicon wafer for non-oxidative heat treatment for use in semiconductor device manufacture according to [any of claim 1 and claim 2] claim 1, wherein the silicon wafer is a silicon wafer for hydrogen heat treatment or a silicon wafer for argon annealing.

5. (amended) A silicon wafer for manufacturing a semiconductor device manufactured by hydrogen heat treatment or argon annealing of the silicon wafer for non-oxidative heat treatment according to [any one of claims 1 to claim 3] claim 1.